



PNP SILICON PLANAR
MEDIUM POWER TRANSISTORS

ISSUE 1 – MARCH 94

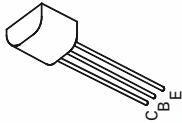
ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	f _T	100			MHz	I _C =-100mA, V _{CE} =-5V f=100MHz
Output Capacitance	C _{obo}			25	pF	V _{CB} =-10V, f=1MHz
Switching Times	t _{on}		300		ns	I _C =-500mA, V _{CC} =-10V I _{B1} =I _{B2} =-50mA
	t _{off}		50		ns	

ZTX549
ZTX549A

FEATURES

- * 30 Volt V_{CEO}
- * 1 Amp continuous current
- * P_{tot} = 1 Watt



E-Line
TO92 Compatible

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ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CBO}	-35	V
Collector-Emitter Voltage	V _{CEO}	-30	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Current	I _{CM}	-2	A
Continuous Collector Current	I _C	-1	A
Power Dissipation: at T _{amb} =25°C derate above 25°C	P _{tot}	1	W
		5.7	mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +200	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-35			V	I _C =-100μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-30			V	I _C =-10mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5			V	I _E =-100μA
Collector Cut-Off Current	I _{CBO}			-0.1 -10	μA	V _{CB} =-30V V _{CE} =-30V, T _{amb} =100°C
	I _{EBO}			-0.1	μA	V _{EB} =-4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.25 -0.50	-0.50 -0.75	V	I _C =-1A, I _B =-100mA*
				-0.30	V	I _C =-2A, I _B =-200mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}		-0.9	-1.25	V	I _C =-100mA, I _B =-1mA*
Base-Emitter Saturation Voltage	V _{BE(on)}		-0.85	-1	V	I _C =-1A, I _B =-100mA*
Static Forward Current Transfer Ratio	h _{FE}	70	200			I _C =50mA, V _{CE} =-2V*
		80	130			I _C =-1A, V _{CE} =-2V*
		40	80			I _C =-2A, V _{CE} =-2V*
		100	160	300		I _C =500mA, V _{CE} =-2V*
ZTX549						I _C =500mA, V _{CE} =-2V*

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

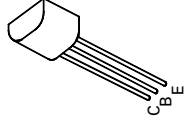
[捷多邦, 专业PCB打样工厂, 24小时加急出货](#)

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

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Output Capacitance	C _{obo}			25	pF	V _{CB} =10V, f=1MHz
Switching Times	t _{on}		300		ns	I _C =500mA, V _{CC} =10V I _{B1} =I _{B2} =50mA
	t _{off}		50		ns	

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Collector Cut-Off Current	I _{CBO}			-0.1 -10	μA μA	V _{CB} =30V V _{CB} =30V, T _{amb} =100°C
Emitter Cut-Off Current	I _{EBO}			-0.1	μA	V _{EB} =4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.25 -0.50	-0.50 -0.75	V V	I _C =1A, I _B =100mA* I _C =2A, I _B =200mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}			-0.30	V	I _C =100mA, I _B =1mA*
			-0.9	-1.25	V	I _C =1A, I _B =100mA*
			-0.85	-1	V	I _C =1A, V _{CE} =2V*
Static Forward Current Transfer Ratio	h _{FE}	70 80 40	200 130 80			I _C =50mA, V _{CE} =2V* I _C =1A, V _{CE} =2V* I _C =2A, V _{CE} =2V*
ZTX549 ZTX549A		100 150	160 200	300 500		I _C =500mA, V _{CE} =2V* I _C =500mA, V _{CE} =2V*

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

ZTX549
ZTX549A

TYPICAL CHARACTERISTICS

